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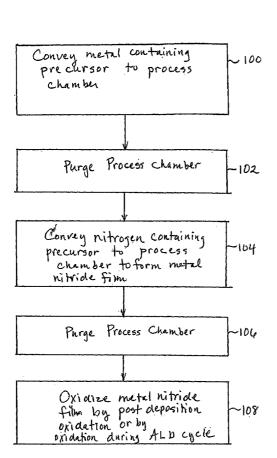
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[Continued on next page]

(54) Title: NITRIDATION OF HIGH-K DIELECTRIC FILMS



(57) Abstract: The present invention promotes incorporation of nitrogen (e.g., nitridation) into high-k dielectric films using a low temperature process. Further, the present invention provides an in-situ method; that is formation of the high-k dielectric film and nitridation of the film are carried out in the same process chamber during deposition of the film, as opposed to the conventional post processing techniques. In another aspect, a method for depositing a multi-layer material for use as a gate dielectric layer in semiconductor devices is provided.

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Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)			
C. DOCUMENTS CONSIDERED TO BE RELEVANT			
Category *	Citation of document, with indication, where appropriate, of the relevant passages		Relevant to claim No.
X,P	US 2004/0198069 (Metzner et al) 7 October 2004 (07.10.2004), Fig. 1, Page 2-6.		1-5, 7, 9, 12-15, 18, 20 and 23
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Y	US 2005/0175789 (Helms Jr. et al) 23 June 2003 (23.06.2003), Page 4, Paragraph 31		8, 19 and 43
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